Power MOSFET 60 V, 78 mΩ, 4.5 A, N–Channel

Automotive Power MOSFET designed to minimize gate charge and low on resistance. AEC–Q101 qualified MOSFET and PPAP capable suitable for automotive applications.

Features

- 4.5 V Drive
- High ESD Protection
- Low On-Resistance
- CPH6 Package is Pin-Compatible with SOT-26
- Pb-Free, Halogen Free and RoHS Compliance

Typical Applications

- Load Switch
- Motor Drive

Specifications

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^{\circ}C$)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V _{DSS}	60	V
Gate to Source Voltage	V _{GSS}	±20	V
Drain Current (DC) (Note 1)	Ι _D	4.5	А
Drain Current (DC) (Note 2)		3.5	А
Drain Current (Pulse) PW \leq 10 µs, duty cycle \leq 1%	I _{DP}	18	A
Power Dissipation Ta = 25°C (Note 1)	P _D	1.9	W
Power Dissipation Ta = 25°C (Note 2)		0.97	W
Junction Temperature and Storage Temperature	Tj, Tstg	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Paramet	er	Symbol	Value	Unit
Junction to Ambient	(Note 1)	$R_{\theta JA}$	78.1	°C/W
	(Note 2)		153	°C/W

1. Surface mounted on ceramic substrate (900 mm² \times 0.8 mm).

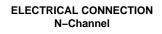
2. Surface mounted on FR4 board using a 92 mm², 1 oz. Cu pad.

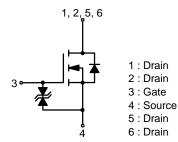


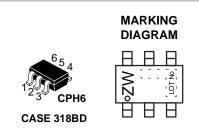
ON Semiconductor®

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V _{DSS}	R _{DS} (on) MAX	I _D MAX
60 V	78 mΩ @ 10 V	4 5 1
	120 mΩ @ 4.5 V	4.5 A







ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	60	-	_	V
Zero-Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	_	-	1.0	μA
Gate to Source Leakage Current	I _{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	_	-	±10	μA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} = 10 V, I _D = 1 mA	1.2	-	2.6	V
Forward Transconductance	9 _{FS}	V _{DS} = 10 V, I _D = 2 A	_	3.0	-	S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D = 2 A, V _{GS} = 10 V	-	60	78	mΩ
		$I_{D} = 1 \text{ A}, \text{ V}_{GS} = 4.5 \text{ V}$	-	84	120	mΩ
Input Capacitance	Ciss	V _{DS} = 20 V, f = 1 MHz	-	505	-	pF
Output Capacitance	Coss		_	57	_	pF
Reverse Transfer Capacitance	Crss		_	37	_	pF
Turn–ON Delay Time	t _d (on)	See Figure 1	_	7.3	-	ns
Rise Time	t _r		_	9.8	-	ns
Turn-OFF Delay Time	t _d (off)		_	40	-	ns
Fall Time	t _f		_	24	-	ns
Total Gate Charge	Qg	V_{DS} = 30 V, V_{GS} = 10 V, I_{D} = 4.5 A	_	10	-	nC
Gate to Source Charge	Qgs]	_	1.6	_	nC
Gate to Drain "Miller" Charge	Qgd	1	_	2.1	-	nC
Forward Diode Voltage	V _{SD}	I _S = 4.5 A, V _{GS} = 0 V	_	0.86	1.2	V

ELECTRICAL CHARACTERISTICS ($T_a = 25^{\circ}C$)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

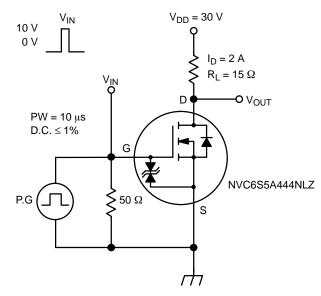
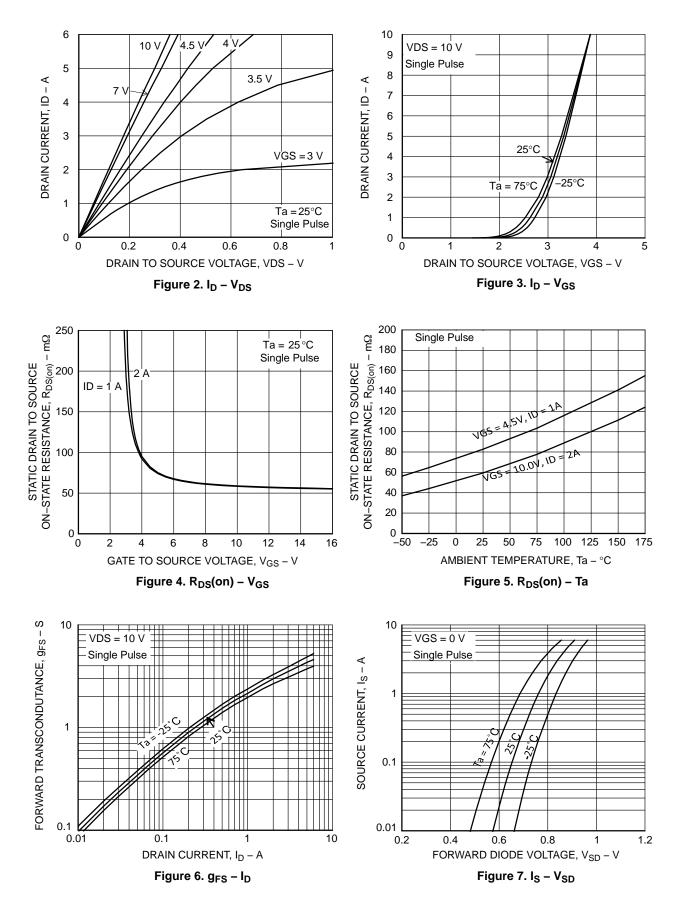
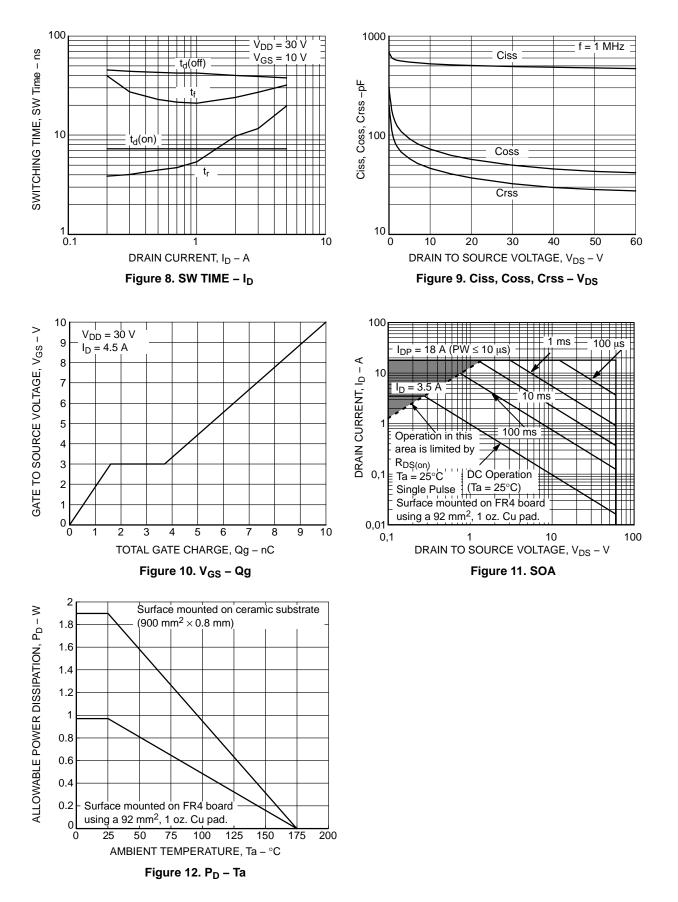


Figure 1. Switching Time Test Circuit

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

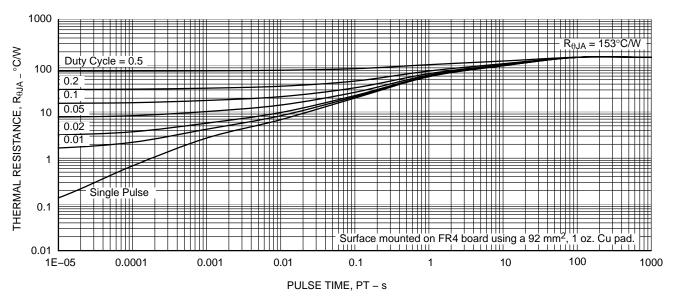


Figure 13. $R_{\theta JA}$ – PULSE TIME

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVC6S5A444NLZT1G	ZW	CPH6 (Pb–Free / Halogen Free)	3,000 / Tape & Reel
NVC6S5A444NLZT2G		(FD-FIEE / Halogen Fiee)	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Since the NVC6S5A444NLZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.



MILLIMETERS

NOM

0.95

0.05

MIN

0.85

0.00

DIM

A A1 DATE 20 SEPT 2024

MAX

1.05

0.10

CPH6 2.90x1.60x0.90, 0.95P CASE 318BD **ISSUE A** D A 2X В *1 *1 E1 Ē *1 2X ___bbb C 2X e 0.25 GAUGE TOP VIEW PLANE END VIEW // eee C - A2 SEATING PLANE С 6X b 🕀 ddd C A B SIDE VIEW

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- ASME Y14.5M, 2018. 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. *1 IS FOR LOT INDICATION

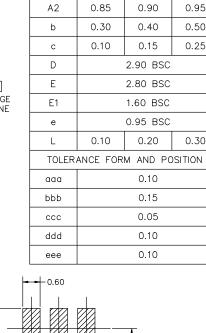


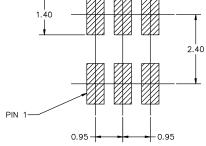
XXX	= Specific Device Code
Μ	= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.





RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please downloadd the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	CPH6 2.90x1.60x0.90, 0.95P		PAGE 1 OF 1	

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